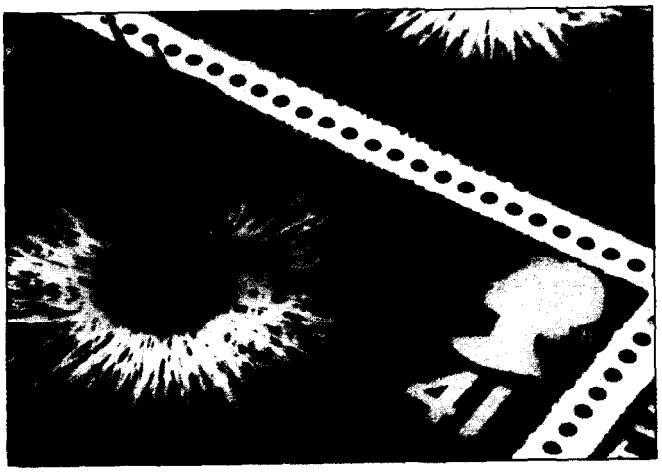
LasIRvis IR emitters



Device News

New IR illuminators are launched by LasIRvis, Sandy, UK, plus publication of a new IR performance products brochure.

The sister pair of emitters comprise the AOE-880-85M and the AOE-940-85M. Both emitters are GaAlAs, based with peak emission wavelengths of 880 nm and 940 nm, respectively.

The emitters are high reliability products manufactured on gold plated mini headers with a low profile epoxy resin lens having a half angle of emission of +/-85° for broad illumination spread. Having a body diameter of only 4.2 mm they boast a continuous forward current capability of 100 mA and will also handle pulses up to 1A.

The radiant intensity is typically 15 mW at a forward current of 50 mA and the temperature range is -30 to 100°C which covers most scientific and industrial environments.

Contact: Ian Bulvas, tel/fax: +44 0 1767 69272/692626. E-mail: lasirvis@kbnet.co.uk

Voltaix appoints Aldrich exclusive

Company News

Dr John P. De Neufville, President of Voltaix, Inc., and Dr Craig A. Recatto, Product Manager of OM Compounds at Aldrich announced the signing of an agreement designating Aldrich as the exclusive worldwide distributor of certain high-purity electronic grade gas products supplied by Voltaix in lecture bottle qualities. These items will be marketed as Aldrich brand products with Voltaix as the exclusive supplier/manufacturer to Aldrich for these items for the duration of the agreement. Both Voltaix and Aldrich will provide complete customer technical support for these items.

Products covered by the agreement include electronic grade Phosphine (29,564-7), Phosphine-d_3 (46,312-4) and others.

Contact: John P. de Neufville of Voltaix, Inc. at 1-800-VOLTAIX or Craig A. Recatto of Aldrich at +1 414-298-7925.

Market for II-VI materials is poised for 9% growth

Markets News

According to a Business Communications Company Inc. report, RGB-196a, "Surging Markets for Silicon Alternative Materials: II-VI Materials and Devices", the worldwide market for II-VI materials and their devices is valued at $111 million in 1996 and is forecasted to grow at an average annual growth rate (AAGR)1 of 9.0%, ultimately accounting for nearly $179 million in revenues by the year 2001. The two principal II-VI materials groups, CdTe and ZnSe, will show growth, but each group will follow its own very distinct path.

BCC points out that market for CdTe-based materials, used principally for IR detection systems, is valued at $108.8 million in 1996 and is projected to increase to $126.8 million in 2001, an AAGR of 3.1%. "The dollar value of materials actually grows stronger than the value of associated devices, as we expect some price moderation in the devices fabricated with the material, caused by a maturation of the technology. However, material costs are expected to remain stable over the 1996-2001 forecast period.

"The market for ZnSe is entering wide open territory. Bulk material is now available for device fabrication, blue LEDs are soon to hit an exploding market, and lifetime problems for blue diode lasers fabricated on the material appear to be solved.

For these reasons, a boom period is predicted for ZnSe materials and ZnSe-based devices." This market is valued at $2.2 million in 1996 and is expected to soar to $52.3 million in 2001, reflecting an AAGR of 85%.

Contact tel/fax: +1 203 853 4266/0348.

Spire projects update

Company News

Spire has received a contract from the DARPA for continued development of a new, high-power, highly-reliable diode laser for use in rapid medical instrument sterilization and haemostasis.

High power laser array modules from robust 1 cm wide diode laser bars fabricated from InGaAsP epi wafers, with 40W average power output, will form the basic building blocks of these laser modules. "These will be incorporated into an innovative, portable battlefield unit for rapid sterilization of medical instruments, and will also be investigated for emergency haemostasis applications" says Kurt Linden, Manager Laser Production Development.

Spire also has a Phase II SBIR contract from Wright Lab for continued investigation of plasma deposition and modelling of thin-film, high-bandgap nitrides.

0961-1290/97/$17.00